Abstracts

Wideband, High Gain, Dual Diode Gunn Amplifier Circuits

J.G. de Koning, R.E. Goldwasser and R.J. Hamilton, Jr.. "Wideband, High Gain, Dual Diode Gunn Amplifier Circuits." 1975 MTT-S International Microwave Symposium Digest of Technical Papers 75.1 (1975 [MWSYM]): 76-78.

Design and performance of wide band, low noise, single stage 10 dB gain Gunn amplifiers in X, Ku and K-band are described. Novel dual diode circuits have been utilized to achieve nearly full band gain with two series connected cathode notch Gunn diodes. Average gains of 9.3 to 11.2 dB have been obtained over 90% of X and Ku-band and 75% of K-band. Noise figures are 15.5 to 18.9 dB.

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